BCD-to-Seven Segment Latch/Decoder/Driver

MC14511B

The MC14511B BCD-to-seven segment latch/decoder/driver is constructed with complementary MOS (CMOS) enhancement mode devices and NPN bipolar output drivers in a single monolithic structure. The circuit provides the functions of a 4-bit storage latch, an 8421 BCD-to-seven segment decoder, and an output drive capability. Lamp test (\overline{LT}), blanking (\overline{BI}), and latch enable (LE) inputs are used to test the display, to turn-off or pulse modulate the brightness of the display, and to store a BCD code, respectively. It can be used with seven-segment light-emitting diodes (LED), incandescent, fluorescent, gas discharge, or liquid crystal readouts either directly or indirectly.

Applications include instrument (e.g., counter, DVM, etc.) display driver, computer/calculator display driver, cockpit display driver, and various clock, watch, and timer uses.

Features

- Low Logic Circuit Power Dissipation
- High-Current Sourcing Outputs (Up to 25 mA)
- Latch Storage of Code
- Blanking Input
- Lamp Test Provision
- Readout Blanking on all Illegal Input Combinations
- Lamp Intensity Modulation Capability
- Time Share (Multiplexing) Facility
- Supply Voltage Range = 3.0 V to 18 V
- Capable of Driving Two Low-power TTL Loads, One Low-power Schottky TTL Load, or Two HTL Loads Over the Rated Temperature Range
- Chip Complexity: 216 FETs or 54 Equivalent Gates
- Triple Diode Protection on all Inputs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb–Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS}) (Note 1)

Symbol	Parameter	Value	Unit
V _{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in}	Input Voltage Range, All Inputs	-0.5 to V _{DD} + 0.5	V
Ι	DC Current Drain per Input Pin	10	mA
PD	Power Dissipation, per Package (Note 2)	500	mW
T _A	Operating Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
I _{OHmax}	Maximum Output Drive Current (Source) per Output	25	mA
POHmax	Maximum Continuous Output Power (Source) per Output (Note 3)	50	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Maximum Ratings are those values beyond which damage to the device may occur.

2. Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C to 125°C

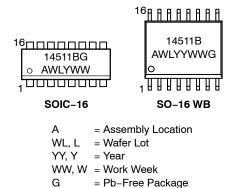
3. $P_{OHmax} = I_{OH} (V_{DD} - V_{OH})$





SOIC-16 D SUFFIX CASE 751B SO-16 WB DW SUFFIX CASE 751G





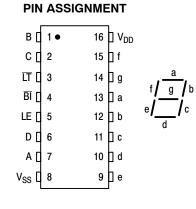
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

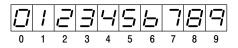
This device contains protection circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high–impedance circuit. A destructive high current mode may occur if V_{in} and V_{out} are not constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Due to the sourcing capability of this circuit, damage can occur to the device if V_{DD} is applied, and the outputs are shorted to V_{SS} and are at a logical 1 (See Maximum Ratings).

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}).



DISPLAY



TRUTH TABLE

			Inp	uts			Outputs							
LE	BI	LT	D	С	в	Α	а	b	С	d	е	f	g	Display
Х	Х	0	Х	Х	Х	Х	1	1	1	1	1	1	1	8
Х	0	1	Х	Х	Х	Х	0	0	0	0	0	0	0	Blank
0 0 0	1 1 1	1 1 1	0 0 0	0 0 0	0 0 1 1	0 1 0 1	1 0 1	1 1 1	1 1 0 1	1 0 1 1	1 0 1 0	1 0 0	0 0 1 1	0 1 2 3
0 0 0	1 1 1	1 1 1	0 0 0	1 1 1	0 0 1 1	0 1 0 1	0 1 0 1	1 0 0 1	1 1 1	0 1 1 0	0 0 1 0	1 1 1 0	1 1 1 0	4 5 6 7
0 0 0	1 1 1	1 1 1	1 1 1	0 0 0	0 0 1 1	0 1 0 1	1 1 0	1 1 0	1 1 0	1 0 0	1 0 0 0	1 1 0	1 1 0	8 9 Blank Blank
0 0 0	1 1 1	1 1 1	1 1 1	1 1 1	0 0 1 1	0 1 0 1	0 0 0 0	0 0 0 0	0 0 0 0	0 0 0 0	0 0 0 0	0 0 0 0	0 0 0	Blank Blank Blank Blank
1	1	1	Х	Х	Х	Х				*				*

X = Don't Care

*Depends upon the BCD code previously applied when LE = 0

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

				- 5	5°C		25°C		12	5°C	
Characteristic		Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 4)	Max	Min	Max	Unit
Output Voltage V _{in} = V _{DD} or 0	"0" Level	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	_ _ _	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
$V_{in} = 0 \text{ or } V_{DD}$	"1" Level	V _{OH}	5.0 10 15	4.1 9.1 14.1	_ _ _	4.1 9.1 14.1	4.57 9.58 14.59	- - -	4.1 9.1 14.1	- - -	Vdc
Input Voltage # $(V_O = 3.8 \text{ or } 0.5 \text{ Vdc})$ $(V_O = 8.8 \text{ or } 1.0 \text{ Vdc})$ $(V_O = 13.8 \text{ or } 1.5 \text{ Vdc})$	"0" Level	V _{IL}	5.0 10 15	- - -	1.5 3.0 4.0		2.25 4.50 6.75	1.5 3.0 4.0		1.5 3.0 4.0	Vdc
$\begin{array}{l} (V_O = 0.5 \mbox{ or } 3.8 \mbox{ Vdc}) \\ (V_O = 1.0 \mbox{ or } 8.8 \mbox{ Vdc}) \\ (V_O = 1.5 \mbox{ or } 13.8 \mbox{ Vdc}) \end{array}$	"1" Level	V _{IH}	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	_ _ _	Vdc
$\begin{array}{l} \text{Output Drive Voltage} \\ (I_{OH} = 0 \text{ mA}) \\ (I_{OH} = 5.0 \text{ mA}) \\ (I_{OH} = 10 \text{ mA}) \\ (I_{OH} = 15 \text{ mA}) \\ (I_{OH} = 20 \text{ mA}) \\ (I_{OH} = 25 \text{ mA}) \end{array}$	Source	V _{OH}	5.0	4.1 _ 3.9 _ 3.4 _	- - - - -	4.1 _ 3.9 _ 3.4 _	4.57 4.24 4.12 3.94 3.70 3.54	- - - - -	4.1 _ 3.5 _ 3.0 _	- - - - -	Vdc
			10	9.1 _ 9.0 _ 8.6 _	- - - - -	9.1 - 9.0 - 8.6 -	9.58 9.26 9.17 9.04 8.90 8.70	- - - - -	9.1 _ 8.6 _ 8.2 _	- - - -	Vdc
			15	14.1 - 14 - 13.6 -	- - - - -	14.1 - 14 - 13.6 -	14.59 14.27 14.18 14.07 13.95 13.70	- - - - -	14.1 - 13.6 - 13.2 -	- - - - -	Vdc
Output Drive Current (V _{OL} = 0.4 V) (V _{OL} = 0.5 V) (V _{OL} = 1.5 V)	Sink	I _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	_ _ _	mAde
Input Current		l _{in}	15	-	± 0.1	-	± 0.00001	± 0.1	-	± 1.0	μAdo
Input Capacitance		C _{in}	-	-	-	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package) V _{in} = 0 α I _{out} = 0 μΑ	or V _{DD} ,	I _{DD}	5.0 10 15	- - -	5.0 10 20	_ _ _	0.005 0.010 0.015	5.0 10 20	_ _ _	150 300 600	μAdo
Total Supply Current (Note (Dynamic plus Quiesce Per Package) (C _L = 50 pF on all outp buffers switching)	ent,	ŀτ	5.0 10 15		-	$I_{T} = (3)$	1.9 μΑ/kHz) f 3.8 μΑ/kHz) f 5.7 μΑ/kHz) f	+ I _{DD}			μAdo

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Noise immunity specified for worst-case input combination. Noise Margin for both "1" and "0" level =

Noise Margin for both 1 and 0 level = 1.0 Vdc min @ V_{DD} = 5.0 Vdc 2.0 Vdc min @ V_{DD} = 10 Vdc 2.5 Vdc min @ V_{DD} = 15 Vdc 5. The formulas given are for the typical characteristics only at 25°C. 6. To calculate total supply current at loads other than 50 pF:

 $I_T(C_L) = I_T(50 \text{ pF}) + 3.5 \times 10^{-3} (C_L - 50) \text{ V}_{DD}f$

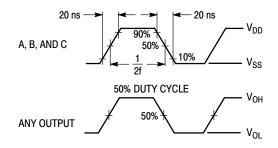
where: I_T is in μA (per package), C_L in pF, V_DD in Vdc, and f in kHz is input frequency.

SWITCHING CHARACTERISTICS (Note 7) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}C$)

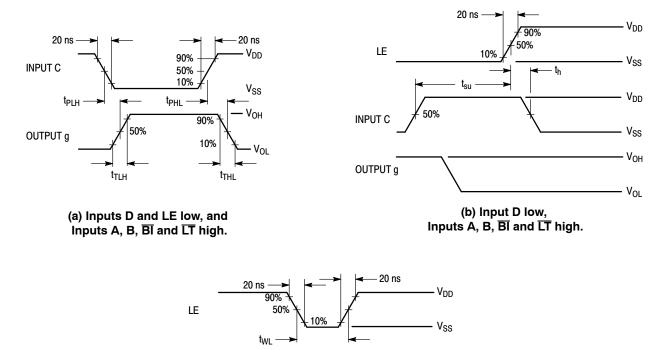
Characteristic	Symbol	V _{DD} Vdc	Min	Тур	Max	Unit
Output Rise Time $t_{TLH} = (0.40 \text{ ns/pF}) \text{ C}_{L} + 20 \text{ ns}$ $t_{TLH} = (0.25 \text{ ns/pF}) \text{ C}_{L} + 17.5 \text{ ns}$ $t_{TLH} = (0.20 \text{ ns/pF}) \text{ C}_{L} + 15 \text{ ns}$	tтLH	5.0 10 15	- - -	40 30 25	80 60 50	ns
Output Fall Time $t_{THL} = (1.5 \text{ ns/pF}) C_L + 50 \text{ ns}$ $t_{THL} = (0.75 \text{ ns/pF}) C_L + 37.5 \text{ ns}$ $t_{THL} = (0.55 \text{ ns/pF}) C_L + 37.5 \text{ ns}$	t _{THL}	5.0 10 15	- - -	125 75 65	250 150 130	ns
Data Propagation Delay Time $t_{PLH} = (0.40 \text{ ns/pF}) \text{ C}_{L} + 620 \text{ ns}$ $t_{PLH} = (0.25 \text{ ns/pF}) \text{ C}_{L} + 237.5 \text{ ns}$ $t_{PLH} = (0.20 \text{ ns/pF}) \text{ C}_{L} + 165 \text{ ns}$	t _{PLH}	5.0 10 15	- -	640 250 175	1280 500 350	ns
$t_{PHL} = (1.3 \text{ ns/pF}) \text{ C}_{L} + 655 \text{ ns}$ $t_{PHL} = (0.60 \text{ ns/pF}) \text{ C}_{L} + 260 \text{ ns}$ $t_{PHL} = (0.35 \text{ ns/pF}) \text{ C}_{L} + 182.5 \text{ ns}$	t _{PHL}	5.0 10 15		720 290 200	1440 580 400	
$\label{eq:Blank} \begin{array}{l} \hline Blank \mbox{Propagation Delay Time} \\ t_{PLH} = (0.30 \mbox{ ns/pF}) C_L + 585 \mbox{ ns} \\ t_{PLH} = (0.25 \mbox{ ns/pF}) C_L + 187.5 \mbox{ ns} \\ t_{PLH} = (0.15 \mbox{ ns/pF}) C_L + 142.5 \mbox{ ns} \\ \end{array}$	t _{PLH}	5.0 10 15	- - -	600 200 150	750 300 220	ns
$t_{PHL} = (0.85 \text{ ns/pF}) \text{ C}_{L} + 442.5 \text{ ns}$ $t_{PHL} = (0.45 \text{ ns/pF}) \text{ C}_{L} + 177.5 \text{ ns}$ $t_{PHL} = (0.35 \text{ ns/pF}) \text{ C}_{L} + 142.5 \text{ ns}$	t _{PHL}	5.0 10 15	- - -	485 200 160	970 400 320	
$\label{eq:Lamp Test Propagation Delay Time} \\ t_{PLH} = (0.45 \mbox{ ns/pF}) \ C_L + 290.5 \mbox{ ns} \\ t_{PLH} = (0.25 \mbox{ ns/pF}) \ C_L + 112.5 \mbox{ ns} \\ t_{PLH} = (0.20 \mbox{ ns/pF}) \ C_L + 80 \mbox{ ns} \\ \end{array}$	telh	5.0 10 15	- - -	313 125 90	625 250 180	ns
t _{PHL} = (1.3 ns/pF) C _L + 248 ns t _{PHL} = (0.45 ns/pF) C _L + 102.5 ns t _{PHL} = (0.35 ns/pF) C _L + 72.5 ns	t _{PHL}	5.0 10 15	- - -	313 125 90	625 250 180	
Setup Time	t _{su}	5.0 10 15	100 40 30	- - -	- - -	ns
Hold Time	t _h	5.0 10 15	60 40 30	- - -	- - -	ns
Latch Enable Pulse Width	t _{WL}	5.0 10 15	520 220 130	260 110 65	- - -	ns

7. The formulas given are for the typical characteristics only.

Input LE low, and Inputs D, \overline{BI} and \overline{LT} high. f in respect to a system clock. All outputs connected to respective C₁ loads.





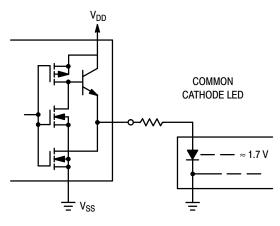


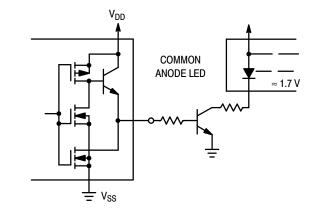
(c) Data DCBA strobed into latches.

Figure 2. Dynamic Signal Waveforms

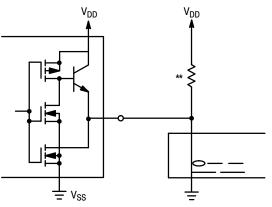
CONNECTIONS TO VARIOUS DISPLAY READOUTS

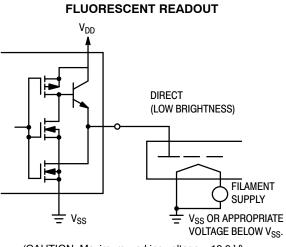
LIGHT EMITTING DIODE (LED) READOUT





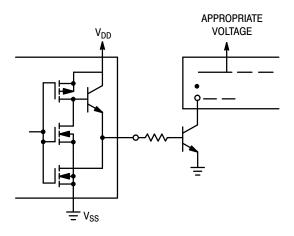
INCANDESCENT READOUT





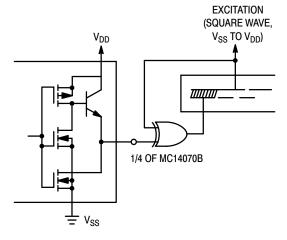
(CAUTION: Maximum working voltage = 18.0 V)

GAS DISCHARGE READOUT



**A filament pre-warm resistor is recommended to reduce filament thermal shock and increase the effective cold resistance of the filament.

LIQUID CRYSTAL (LCD) READOUT



Direct DC drive of LCD's not recommended for life of LCD readouts.

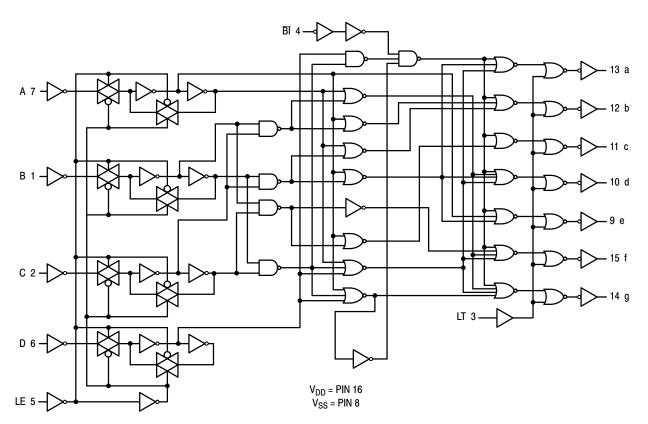


Figure 3. Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]
MC14511BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14511BDR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC14511BDWR2G	SO-16 WB (Pb-Free)	1000 / Tape & Reel
NLV14511BDWR2G*	SO-16 WB (Pb-Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable.

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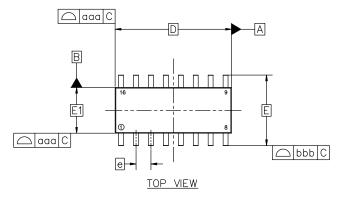
SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

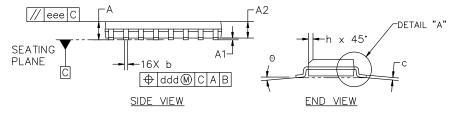
DATE 29 MAY 2024

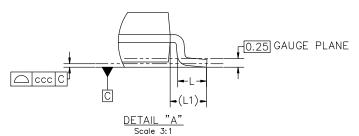
DURSEM

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.

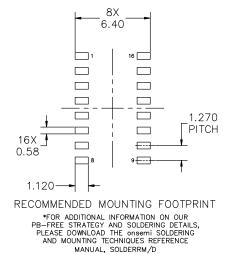






DIM	MIN	NOM	MAX				
A	1.35	1.55	1.75				
A1	0.00	0.05	0.10				
A2	1.35	1.50	1.65				
b	0.35	0.42	0.49				
с	0.19	0.22	0.25				
D		9.90 BSC					
E		6.00 BSC					
E1	3.90 BSC						
е	1.27 BSC						
h	0.25		0.50				
L	0.40	0.83	1.25				
L1		1.05 REF					
Θ	0.		7'				
TOLERAN	CE OF FC	ORM AND	POSITION				
aaa	0.10						
bbb	0.20						
ссс	0.10						
ddd		0.25					
eee		0.10					

MILLIMETERS



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DATE 29 MAY 2024

GENERIC MARKING DIAGRAM*

16	F	A	H	A	H	A	A	A	
		XX							
		XX	XX)	XX	XX)	XX	XX	X	
	0		A١	WL.	ΥW	W			
1	Ŧ	H	H	H	H	H	H	Ŧ	I

XXXXX = Specific Device Code

A = Assembly Location

- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.		PIN 1.	COLLECTOR, DYE #1
2.	BASE	2.	ANODE	2.	BASE, #1	2.	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	
4.	NO CONNECTION	4.	CATHODE	4.		4.	
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH		
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT)	
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT)	
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH		
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT)	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT)	
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPUT)	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH		
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH		
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT)	
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT)	
12.	SOURCE, #3	12.	ANODE	12.)	
13.	GATE, #2		ANODE	13.			
14.	SOURCE, #2		ANODE	14.			
15.	GATE, #1	15.	ANODE	15.)	
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH		

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

SOIC-16 WB CASE 751G ISSUE E SCALE 1:1 NOTES A DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 1. CONTROLLING DIMENSION: MILLIMETERS 2. 16 🗢 0.25@ B@ В DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. з. <u>A A A A</u> RRRR ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS. 4. MAXIMUM MOLD PROTRUSION OR FLASH TO BE 0.15 PER SIDE. 5. MILLIMETERS DIM MIN. MAX. H Н Α 2.35 2.65 h 8 45 0.25 A1 0.10 -16X B e DETAIL A в 0.35 0.49 0.2500 TAS BS END VIEW С 0.23 0.32 TOP VIEW D 10.15 10.45 7.40 7.60 Е 1.27 BSC e 16X н 10.05 10.55 -L h 0.53 REF SEATIN **A1** 0.50 0.90 L SIDE VIEW М 0* 7* DETAIL A 2X SCALE 0000|0000 GENERIC 11.00 **MARKING DIAGRAM*** 1 16X 1.62 .27 XXXXXXXXXXXX PITCH XXXXXXXXXXXX RECOMMENDED AWLYYWWG MOUNTING FOOTPRINT H H Η 1 H Н XXXXX = Specific Device Code = Assembly Location А = Wafer Lot WL YY = Year ww = Work Week G = Pb-Free Package *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may

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